

**AUTOMOTIVE MOSFET**

# IRF7484Q

HEXFET® Power MOSFET

**Typical Applications**

- Relay replacement
- Anti-lock Braking System
- Air Bag

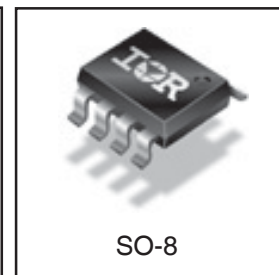
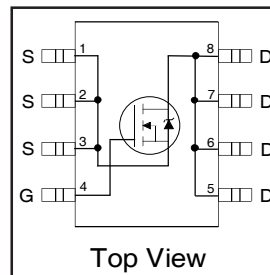
**Benefits**

- Advanced Process Technology
- Ultra Low On-Resistance
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax

V <sub>DSS</sub>	R <sub>DS(on)</sub> max (mΩ)	I <sub>D</sub>
40V	10@V <sub>GS</sub> = 7.0V	14A

**Description**

Specifically designed for Automotive applications, this Stripe Planar design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this HEXFET power MOSFET are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These benefits combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



**Absolute Maximum Ratings**

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	14	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	11	
I <sub>DM</sub>	Pulsed Drain Current ①	110	A
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Power Dissipation ③	2.5	W
	Linear Derating Factor	0.02	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 8.0	V
E <sub>AS</sub>	Single Pulse Avalanche Energy ④	230	mJ
I <sub>AR</sub>	Avalanche Current ①	See Fig.16c, 16d, 19, 20	A
E <sub>AR</sub>	Repetitive Avalanche Energy ④		mJ
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range	-55 to + 150	°C

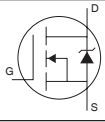
**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJL</sub>	Junction-to-Drain Lead	—	20	°C/W
R <sub>θJA</sub>	Junction-to-Ambient ③	—	50	

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

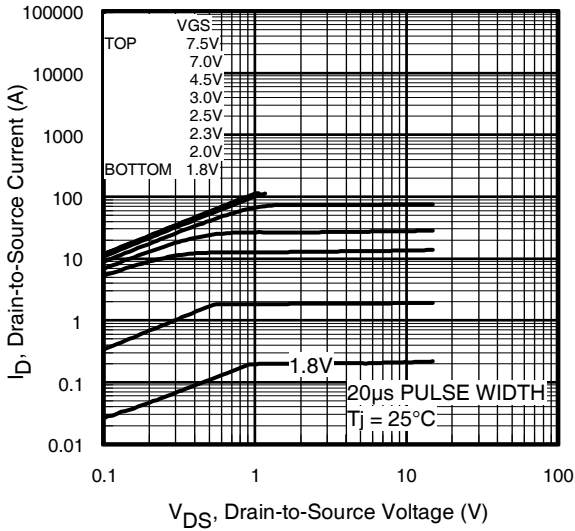
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.040	—	V/°C	Reference to $25^\circ\text{C}$ , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	10	mΩ	$V_{GS} = 7.0V, I_D = 14A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	40	—	—	S	$V_{DS} = 10V, I_D = 14A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 32V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 8.0V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -8.0V$
$Q_g$	Total Gate Charge	—	69	100	nC	$I_D = 14A$
$Q_{gs}$	Gate-to-Source Charge	—	9.0	—		$V_{DS} = 32V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	16	—		$V_{GS} = 7.0V$
$t_{d(on)}$	Turn-On Delay Time	—	9.3	—	ns	$V_{DD} = 20V$ ②
$t_r$	Rise Time	—	5.0	—		$I_D = 1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	180	—		$R_G = 6.2\Omega$
$t_f$	Fall Time	—	58	—		$V_{GS} = 7.0V$
$C_{iss}$	Input Capacitance	—	3520	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	660	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	76	—		$f = 1.0MHz$

## Source-Drain Ratings and Characteristics

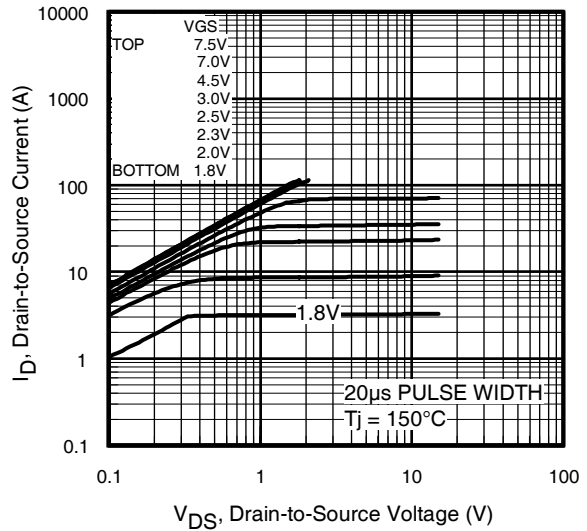
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	110		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 2.3A, V_{GS} = 0V$ ②
$t_{rr}$	Reverse Recovery Time	—	59	89	ns	$T_J = 25^\circ\text{C}, I_F = 2.3A$
$Q_{rr}$	Reverse Recovery Charge	—	110	170	nC	$di/dt = 100A/\mu s$ ②

### Notes:

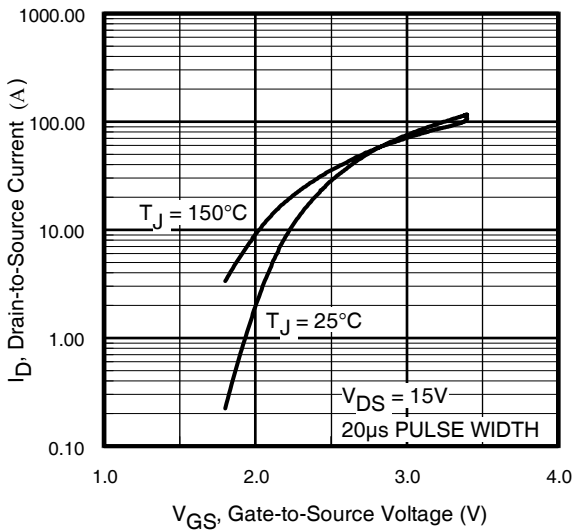
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ③ Surface mounted on 1 in square Cu board.
- ④ Starting  $T_J = 25^\circ\text{C}$ ,  $L = 2.3mH$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 14A$ . (See Figure 12).
- ⑤  $I_{SD} \leq 14A$ ,  $di/dt \leq 140A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 150^\circ\text{C}$ .
- ⑥ Limited by  $T_{Jmax}$ , see Fig.16c, 16d, 19, 20 for typical repetitive avalanche performance.



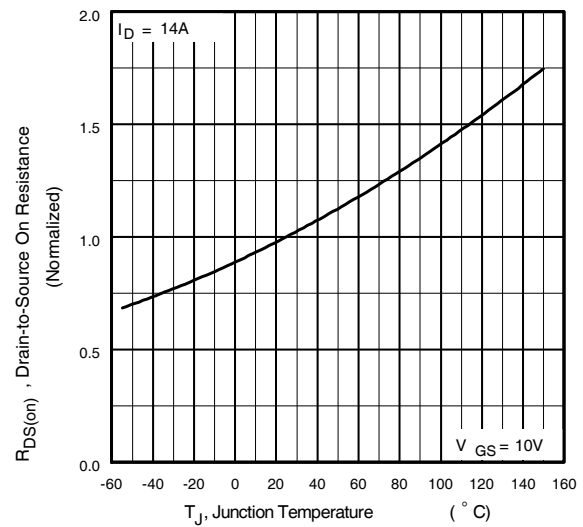
**Fig 1.** Typical Output Characteristics



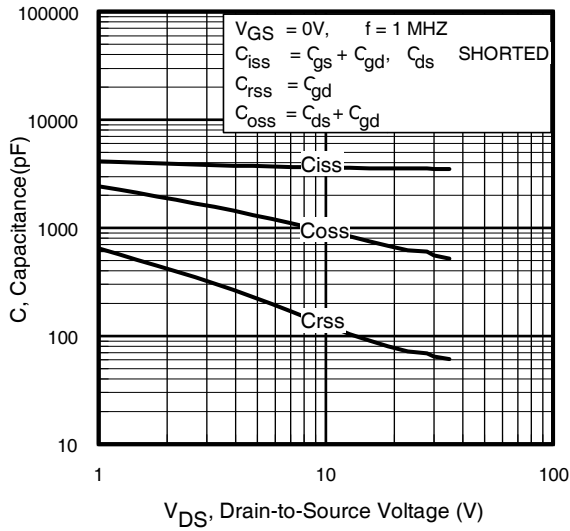
**Fig 2.** Typical Output Characteristics



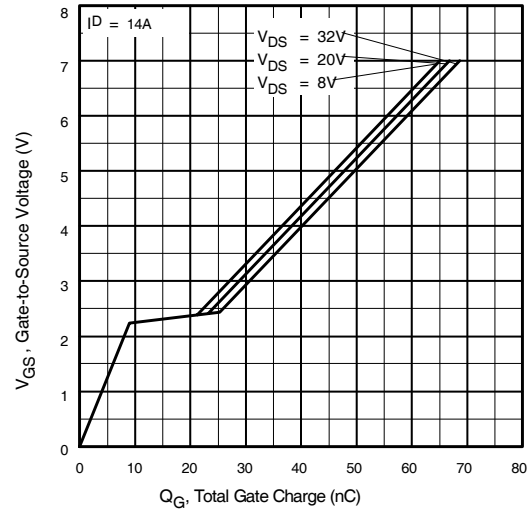
**Fig 3.** Typical Transfer Characteristics



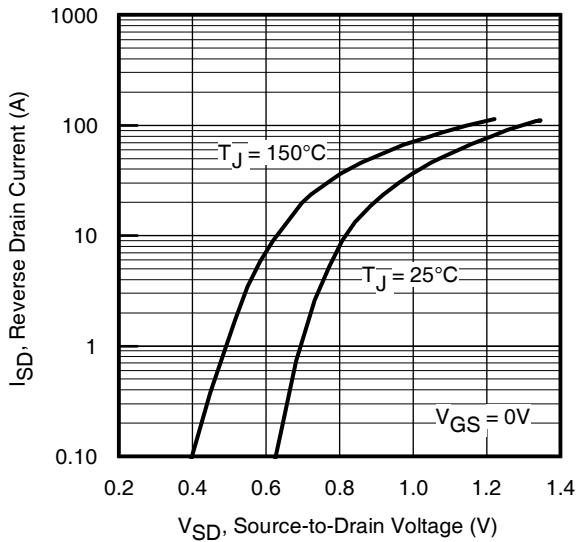
**Fig 4.** Normalized On-Resistance Vs. Temperature



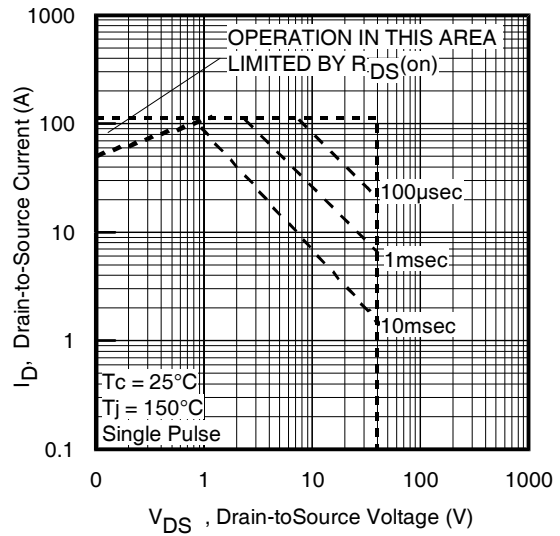
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



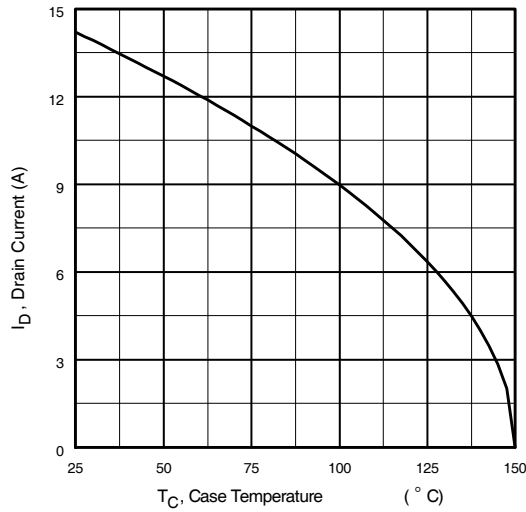
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



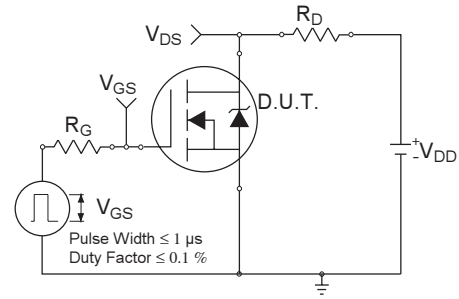
**Fig 7.** Typical Source-Drain Diode Forward Voltage



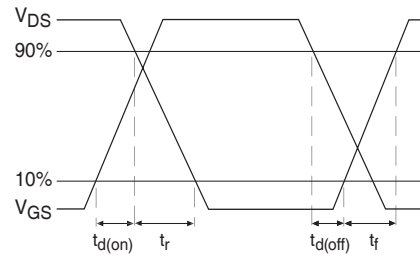
**Fig 8.** Maximum Safe Operating Area



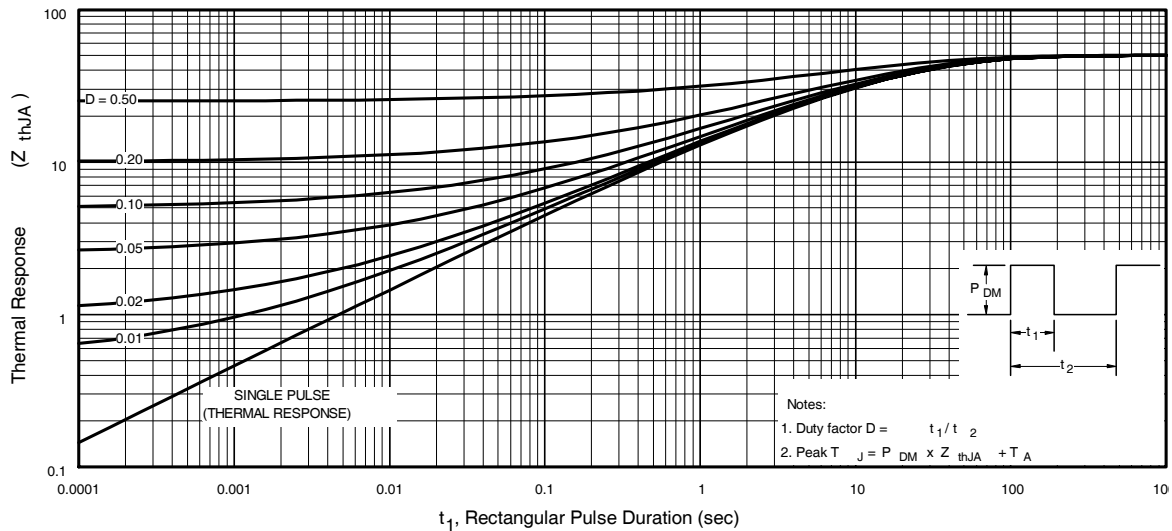
**Fig 9.** Maximum Drain Current Vs. Case Temperature



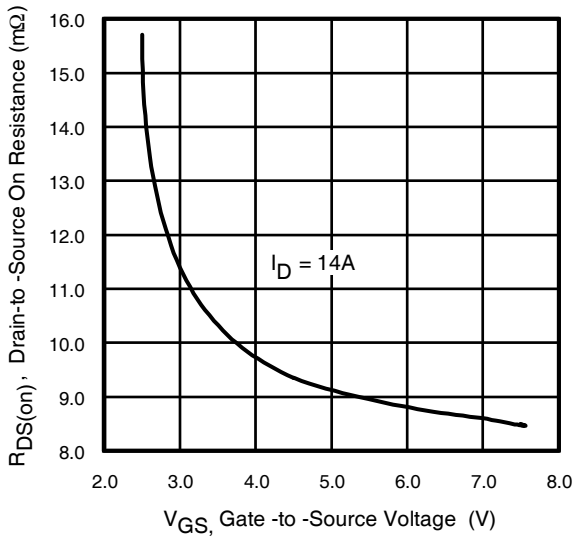
**Fig 10a.** Switching Time Test Circuit



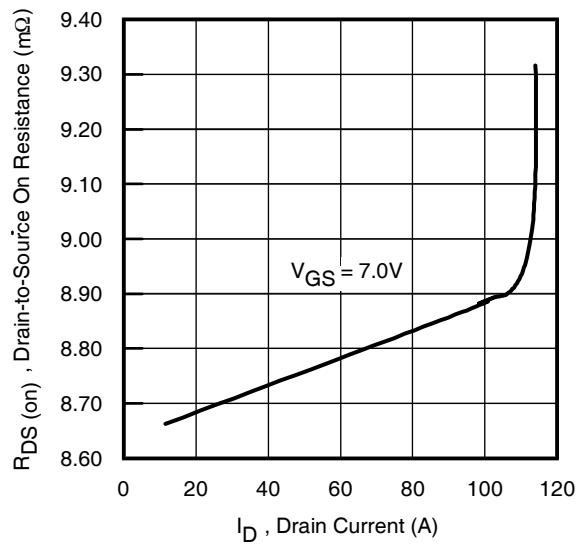
**Fig 10b.** Switching Time Waveforms



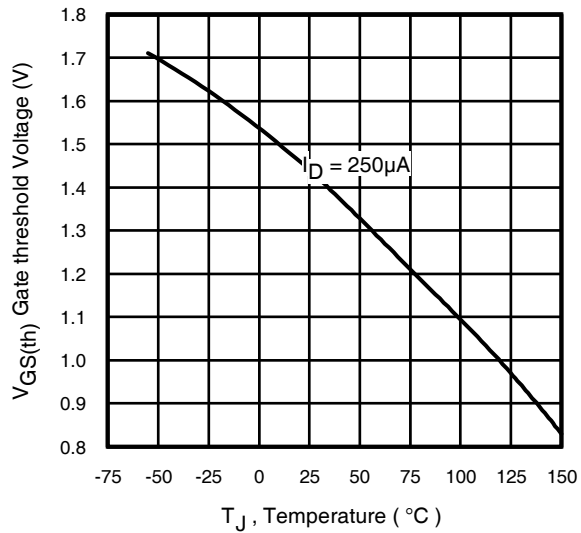
**Fig 11.** Typical Effective Transient Thermal Impedance, Junction-to-Ambient



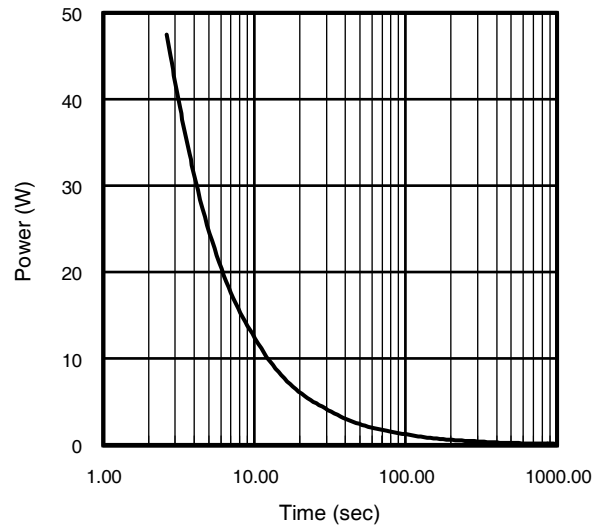
**Fig 12.** Typical On-Resistance Vs. Gate Voltage



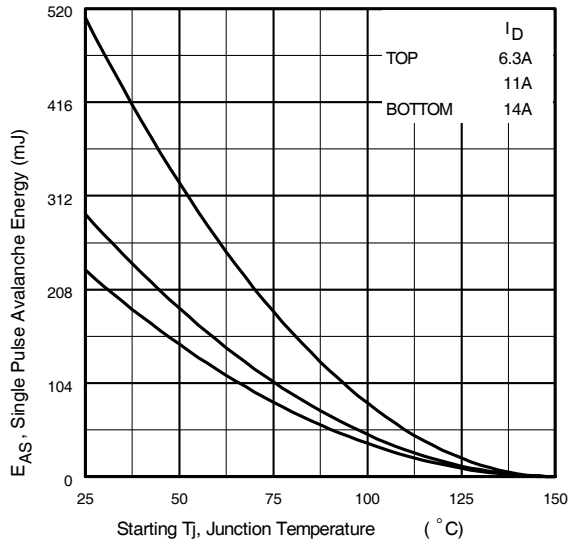
**Fig 13.** Typical On-Resistance Vs. Drain Current



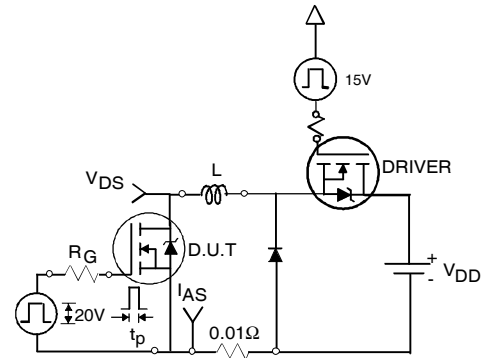
**Fig 14.** Typical Threshold Voltage Vs. Junction Temperature



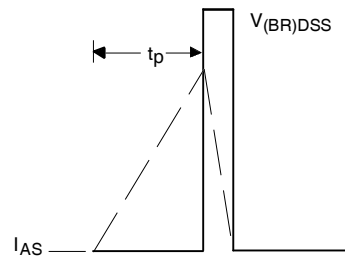
**Fig 15.** Typical Power Vs. Time



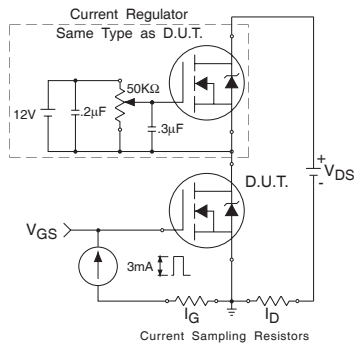
**Fig 16a.** Maximum Avalanche Energy Vs. Drain Current



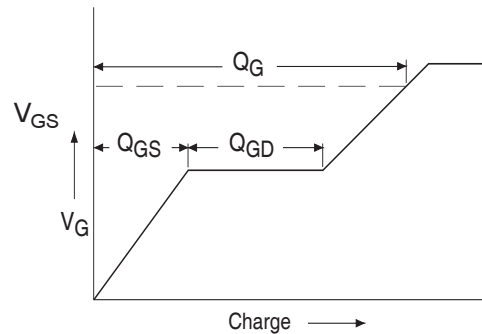
**Fig 16c.** Unclamped Inductive Test Circuit



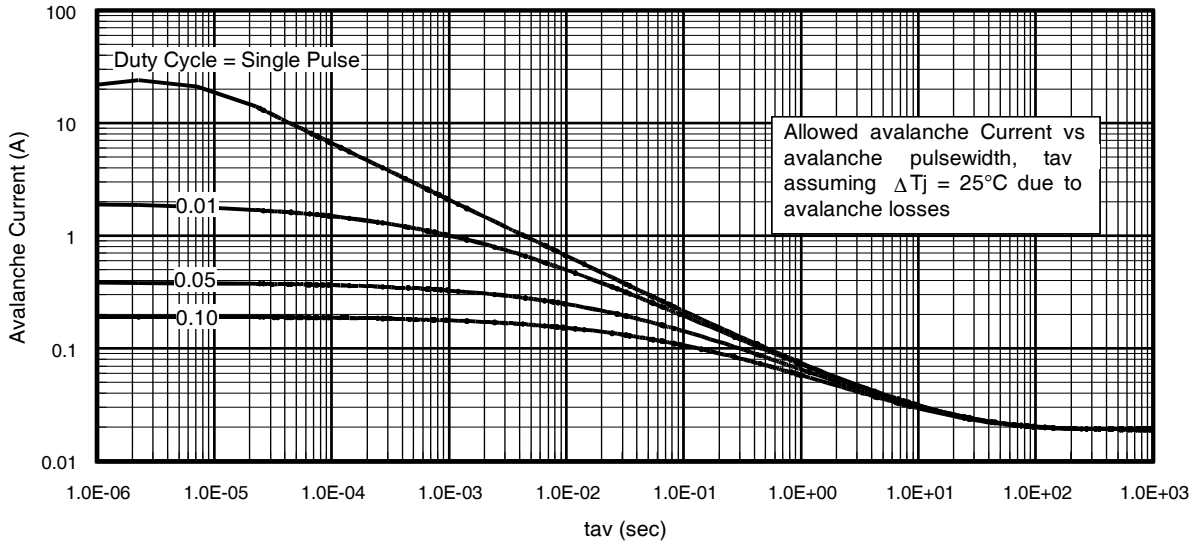
**Fig 16d.** Unclamped Inductive Waveforms



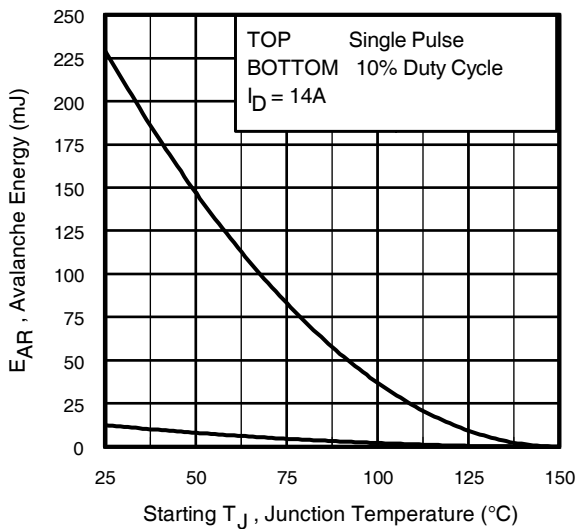
**Fig 17.** Gate Charge Test Circuit



**Fig 18.** Basic Gate Charge Waveform



**Fig 19.** Typical Avalanche Current Vs.Pulsewidth



**Fig 20.** Maximum Avalanche Energy Vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 15, 16:**  
**(For further info, see AN-1005 at [www.irf.com](http://www.irf.com))**

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5.  $BV$  = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as  $25^\circ\text{C}$  in Figure 15, 16).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see figure 11)

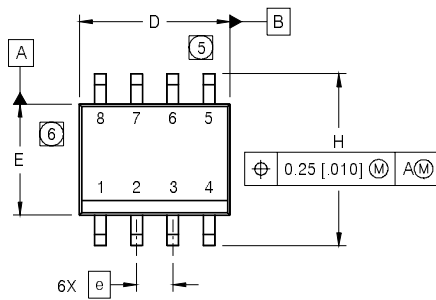
$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

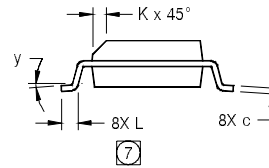
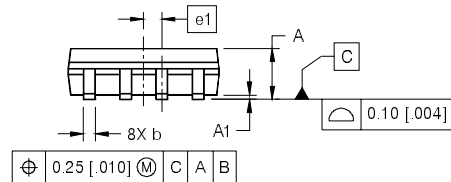
$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$



## SO-8 Package Details



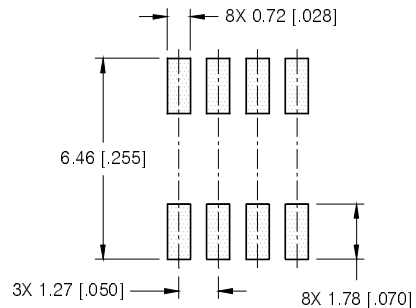
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



**NOTES:**

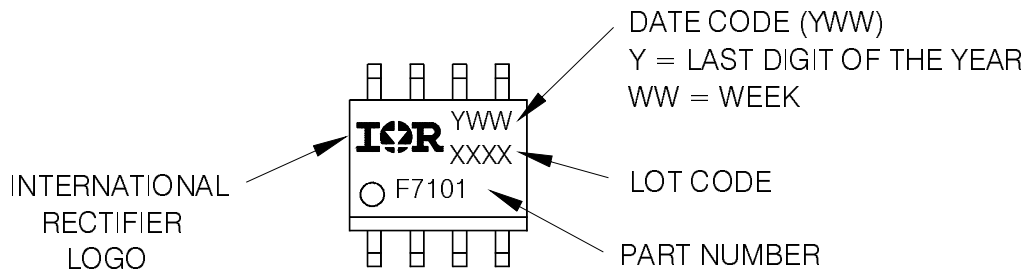
- DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- CONTROLLING DIMENSION: MILLIMETER
- DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

**FOOTPRINT**



## SO-8 Part Marking

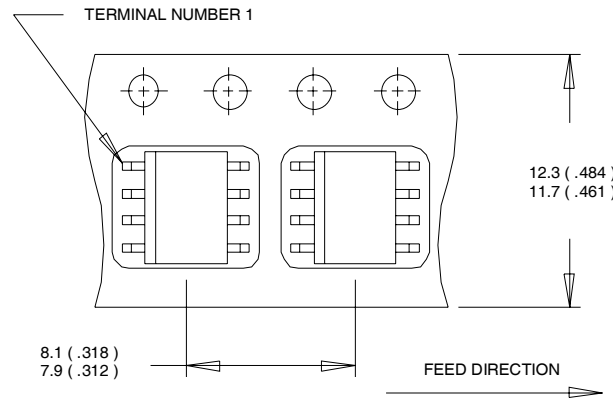
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



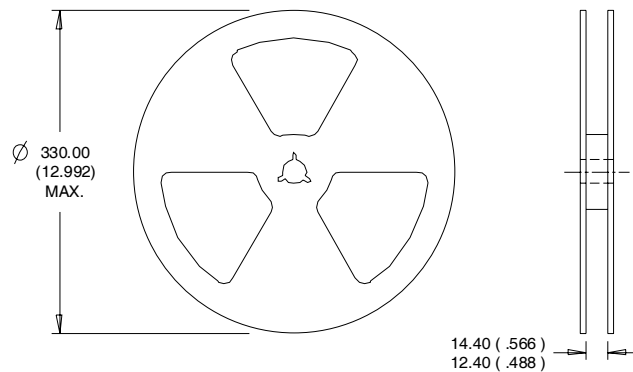
# IRF7484Q

International  
**IR** Rectifier

## SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Automotive [Q101] market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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